National Semiconductor is now part of Texas Instruments.

Search http://www.ti.com/ for the latest technical information and details on our current products and services.



LM136A-2.5QML

2.5V Reference Diode

General Description

The LM136A-2.5QML integrated circuit is a precision 2.5V shunt regulator diode. This monolithic IC voltage reference operates as a low-temperature-coefficient 2.5V zener with 0.2 Ω dynamic impedance. A third terminal on the LM136A-2.5QML allows the reference voltage and temperature coefficient to be trimmed easily.

The LM136A-2.5QML is useful as a precision 2.5V low voltage reference for digital voltmeters, power supplies or op amp circuitry. The 2.5V make it convenient to obtain a stable reference from 5V logic supplies. Further, since the LM136A-2.5QML operates as a shunt regulator, it can be used as either a positive or negative voltage reference.

Features

- Available with radiation guarantee
 - Total Ionizing Dose

100 krad(Si)

— ELDRS Free

- 100 krad(Si)
- Low temperature coefficient
- Wide operating current of 400 µA to 10 mA
- Guaranteed temperature stability
- Easily trimmed for minimum temperature drift
- Fast turn-on
- 3-lead transistor package

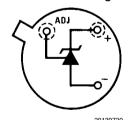
Ordering Information

NS Part Number	SMD Part Number	NS Package Number	Package Description
LM136AH-2.5/883		H03H	T0-46, 3LD Metal Can
LM136AH-2.5RQV (<i>Note 6</i>)	5962R0050101VXA 100 krad(Si)	Н03Н	T0-46, 3LD Metal Can
LM136AH-2.5RLQV (<i>Note 7</i>) ELDRS Free	5962R0050102VXA 100 krad(Si)	Н03Н	T0-46, 3LD Metal Can
LM136-2.5 MDE (<i>Note 7</i>) ELDRS Free	5962R0050102V9A 100 krad(Si)	(Note 1)	Bare Die
LM136-2.5 MDR (<i>Note 6</i>)	5962R0050101V9A 100 krad(Si)	(Note 1)	Bare Die

Note 1: FOR ADDITIONAL DIE INFORMATION, PLEASE VISIT THE HI REL WEB SITE AT: www.national.com/analog/space/level_die

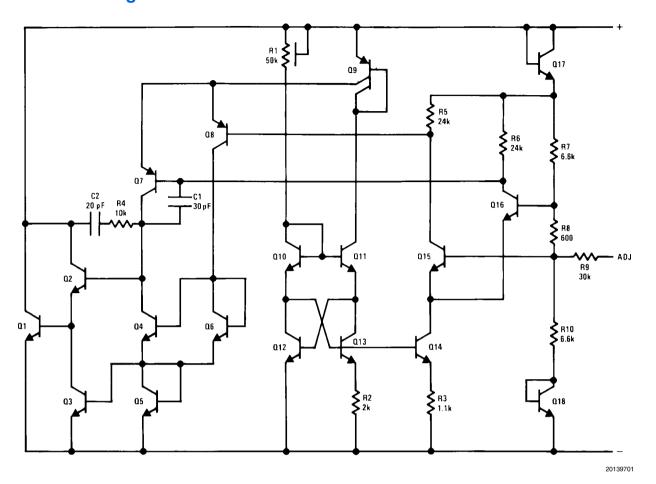
Connection Diagram

TO-46 Metal Can Package



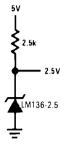
Bottom View See NS Package Number H03H

Schematic Diagram



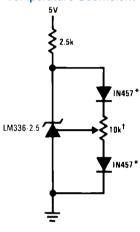
Typical Applications

2.5V Reference



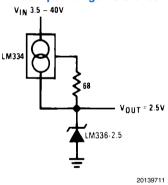
20139709

2.5V Reference with Minimum Temperature Coefficient



20139710

Wide Input Range Reference



[†]Adjust to 2.490V *Any silicon signal diode

Absolute Maximum Ratings (Note 2)

Reverse Current 15 mA Forward Current 10 mA

Storage Temperature $-60^{\circ}\text{C} \le \text{T}_{\text{A}} \le +150^{\circ}\text{C}$

Operating Temperature Range (*Note 3*) $-55^{\circ}\text{C} \le \text{T}_{\text{A}} \le +125^{\circ}\text{C}$ Maximum Junction Temperature (T_.) (*Note 3*) $+150^{\circ}\text{C}$

Lead Temperature (Soldering 10 seconds)

300°C

Thermal Resistance

 θ_{JA}

Still Air Flow 354°C/W 500LF/Min Air Flow 77°C/W

 θ_{JC} 46°C/W ESD Rating (*Note 4*) 1,000V

Quality Conformance Inspection

Mil-Std-883, Method 5005 - Group A

Subgroup	Subgroup Description	
1	Static tests at	+25
2	Static tests at	+125
3	Static tests at	-55
4	Dynamic tests at	+25
5	Dynamic tests at	+125
6	Dynamic tests at	-55
7	Functional tests at	+25
8A	Functional tests at	+125
8B	Functional tests at	-55
9	Switching tests at	+25
10	Switching tests at	+125
11	Switching tests at	-55
12	Settling time at	+25
13	Settling time at	+125
14	Settling time at	-55

LM136A-2.5QML Electrical Characteristics

DC Parameters

The following conditions apply, unless otherwise specified. $I_{B} = 1 \text{mA}$

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub- groups
I _{Adj}	Adjust Current	$V_{Adj} = 0.7V$		-125	+125	μΑ	1, 2, 3
ΔV_Z	Delta Zener Voltage	0.455.4 < 10.55.4			6.0	mV	1
	Delta Zeriei Voltage	$0.4\text{mA} \le I_Z \le 10 \text{ mA}$			10	mV	2, 3
	Zener Voltage	V _{Adj} = Open		2.465	2.515	٧	1
				2.44	2.54	V	2, 3
V _Z		V _{Adj} = 0.7V		2.39	2.49	V	1
				2.29	2.49	٧	2, 3
		$V_{Adj} = 1.9V$		2.49	2.69	V	1, 2, 3
7	Bayaraa Dynamia Impadanaa		(Note 5)		0.6	Ω	1
Z _{RD}	Reverse Dynamic Impedance		(Note 5)		1.0	Ω	2, 3
V _{Stab}	Temperature Stability	V _Z = Adjusted to 2.490V			18	mV	2, 3

DC Drift Parameters

Delta calculations are performed on QMLV devices at Group B, Subgroup 5 only.

Symbol	Parameter	Conditions	Notes	Min	Max	Unit	Sub- groups
V _z	Zener Voltage	V _{Adj} = Open		-10	+10	mV	1
		$V_{Adj} = 0.7V$		-10	+10	mV	1
		$V_{Adj} = 1.9V$		-10	+10	mV	1

Note 2: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits. For guaranteed specifications and test conditions, see the Electrical Characteristics. The guaranteed specifications apply only for the test conditions listed. Some performance characteristics may degrade when the device is not operated under the listed test conditions.

Note 3: The maximum power dissipation must be derated at elevated temperatures and is dictated by $T_{J_{max}}$ (maximum junction temperature), θ_{J_A} (package junction to ambient thermal resistance), and T_A (ambient temperature). The maximum allowable power dissipation at any temperature is $P_{Dmax} = (T_{Jmax} - T_A)/\theta_{JA}$ or the number given in the Absolute Maximum Ratings, whichever is lower.

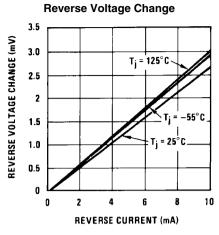
Note 4: Human body model, $1.5 \text{K}\Omega$ in series with 100pF.

Note 5: Parameter tested go-no-go only.

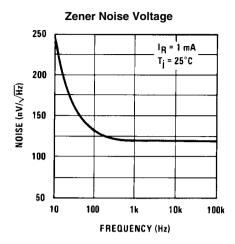
Note 6: Pre and post irradiation limits are identical to those listed under DC electrical characteristics. These parts may be dose rate sensitive in a space environment and may demonstrate enhanced low dose rate effect. Radiation end point limits for the noted parameters are guaranteed only for the conditions as specified in Mil-Std-883, Method 1019.

Note 7: Low dose rate testing has been performed on a wafer-by-wafer basis, per test method 1019 condition D of MIL-STD-883, with no enhanced low dose rate sensitivity (ELDRS) effect.

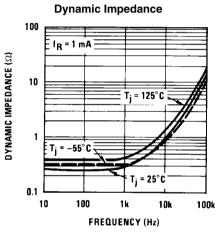
Typical Performance Characteristics



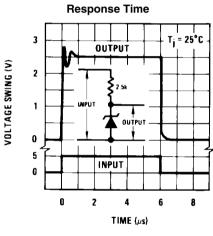
20139721



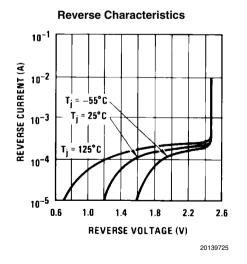
20139722



20139723



20139724



Forward Characteristics

1.2

1.0

0.8

0.6

T_j = -55°C

0.001

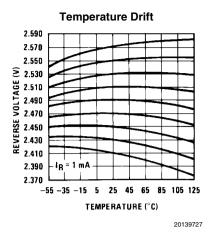
0.01

0.01

0.01

FORWARD CURRENT (mA)

20139726



Application Hints

The LM136 voltage reference is much easier to use than ordinary zener diodes. It's low impedance and wide operating current range simplify biasing in almost any circuit. Further, either the breakdown voltage or the temperature coefficient can be adjusted to optimize circuit performance.

Figure 1 shows an LM136 with a 10k potentiometer for adjusting the reverse breakdown voltage. With the addition of R1 the breakdown voltage can be adjusted without affecting the temperature coefficient of the device. The adjustment range is usually sufficient to adjust for both the initial device tolerance and inaccuracies in buffer circuitry.

If minimum temperature coefficient is desired, two diodes can be added in series with the adjustment potentiometer as shown in *Figure 2*. When the device is adjusted to 2.490V the temperature coefficient is minimized. Almost any silicon signal diode can be used for this purpose such as a 1N914, 1N4148 or a 1N457. For proper temperature compensation the diodes should be in the same thermal environment as the LM136. It is usually sufficient to mount the diodes near the LM136 on the printed circuit board. The absolute resistance of R1 is not critical and any value from 2k to 20k will work.

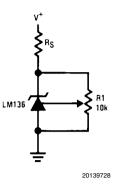


FIGURE 1. LM136 With Pot for Adjustment of Breakdown Voltage (Trim Range = ±120 mV typical)

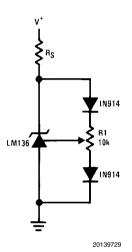
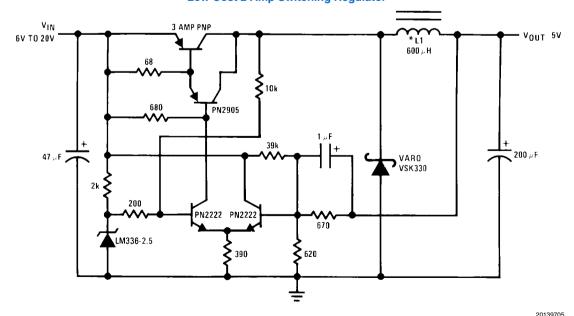


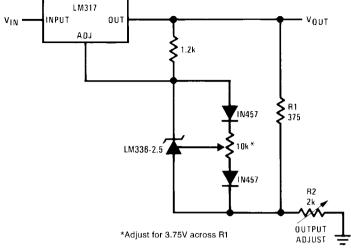
FIGURE 2. Temperature Coefficient Adjustment (Trim Range = ±70 mV typical)

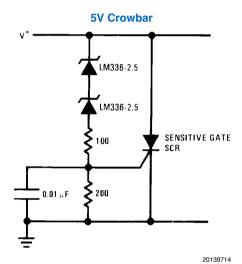
Low Cost 2 Amp Switching Regulator[†]



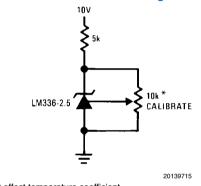
*L1 60 turns #16 wire on Arnold Core A-254168-2 †Efficiency ≈ 80%

Precision Power Regulator with Low Temperature Coefficient



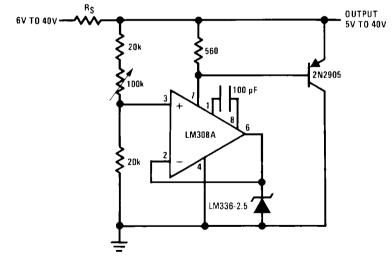


Trimmed 2.5V Reference with Temperature Coefficient Independent of Breakdown Voltage



*Does not affect temperature coefficient

Adjustable Shunt Regulator

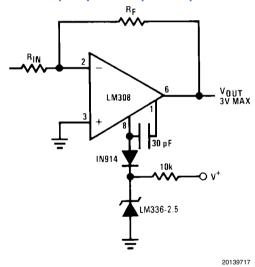


20139706

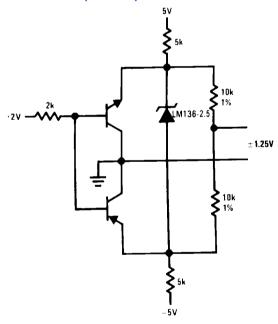
2.5k 25k 250k 2.5M 11% 10k/V LM336-2.5 CALIBRATE 1 MEG/V LM312 6 VOUT

20139716

Op Amp with Output Clamped

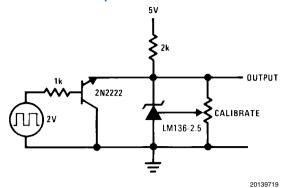


Bipolar Output Reference

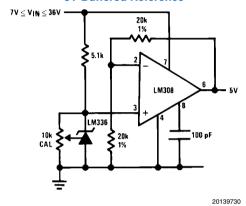


20139718

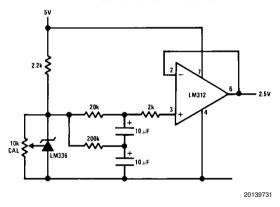
2.5V Square Wave Calibrator



5V Buffered Reference



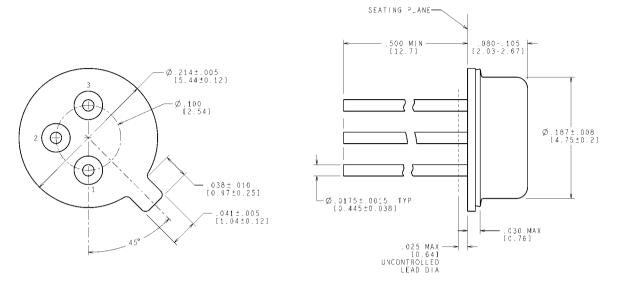
Low Noise Buffered Reference



Revision History

Date Released	Revision	Section	Changes
07/06/07	Α	New Release, Corporate format	2 MDS datasheets converted into one corporate
			datasheet format. MNLM136-2.5-X Rev 0A0 and
			MNLM136A-2.5–X-RH. The ELDRS Part has also
			been added. Rev. 0E0 will be archived.
10/16/2010	В	Data Sheet Title, General Description, Order	Update with current device information and format.
		Information, Electrical Characteristics,	Removed all references to the LM136-2.5 Non "A"
		Application Hints	package NSID no longer offered. Added Die NSID's
			to data sheet. Revision A will be Archived.

Physical Dimensions inches (millimeters) unless otherwise noted



CONTROLLING DIMENSION IS INCH VALUES IN [] ARE IN MILLIMETERS

H03H (Rev F)

NS Package Number H03H

Notes

For more National Semiconductor product information and proven design tools, visit the following Web sites at:

Pro	oducts	Design Support		
Amplifiers	www.national.com/amplifiers	WEBENCH® Tools	www.national.com/webench	
Audio	www.national.com/audio	App Notes	www.national.com/appnotes	
Clock and Timing	www.national.com/timing	Reference Designs	www.national.com/refdesigns	
Data Converters	www.national.com/adc	Samples	www.national.com/samples	
Interface	www.national.com/interface	Eval Boards	www.national.com/evalboards	
LVDS	www.national.com/lvds	Packaging	www.national.com/packaging	
Power Management	www.national.com/power	Green Compliance	www.national.com/quality/green	
Switching Regulators	www.national.com/switchers	Distributors	www.national.com/contacts	
LDOs	www.national.com/ldo	Quality and Reliability	www.national.com/quality	
LED Lighting	www.national.com/led	Feedback/Support	www.national.com/feedback	
Voltage References	www.national.com/vref	Design Made Easy	www.national.com/easy	
PowerWise® Solutions	www.national.com/powerwise	Applications & Markets	www.national.com/solutions	
Serial Digital Interface (SDI)	www.national.com/sdi	Mil/Aero	www.national.com/milaero	
Temperature Sensors	www.national.com/tempsensors	SolarMagic™	www.national.com/solarmagic	
PLL/VCO	www.national.com/wireless	PowerWise® Design University	www.national.com/training	

THE CONTENTS OF THIS DOCUMENT ARE PROVIDED IN CONNECTION WITH NATIONAL SEMICONDUCTOR CORPORATION ("NATIONAL") PRODUCTS. NATIONAL MAKES NO REPRESENTATIONS OR WARRANTIES WITH RESPECT TO THE ACCURACY OR COMPLETENESS OF THE CONTENTS OF THIS PUBLICATION AND RESERVES THE RIGHT TO MAKE CHANGES TO SPECIFICATIONS AND PRODUCT DESCRIPTIONS AT ANY TIME WITHOUT NOTICE. NO LICENSE, WHETHER EXPRESS, IMPLIED, ARISING BY ESTOPPEL OR OTHERWISE, TO ANY INTELLECTUAL PROPERTY RIGHTS IS GRANTED BY THIS DOCUMENT.

TESTING AND OTHER QUALITY CONTROLS ARE USED TO THE EXTENT NATIONAL DEEMS NECESSARY TO SUPPORT NATIONAL'S PRODUCT WARRANTY. EXCEPT WHERE MANDATED BY GOVERNMENT REQUIREMENTS, TESTING OF ALL PARAMETERS OF EACH PRODUCT IS NOT NECESSARILY PERFORMED. NATIONAL ASSUMES NO LIABILITY FOR APPLICATIONS ASSISTANCE OR BUYER PRODUCT DESIGN. BUYERS ARE RESPONSIBLE FOR THEIR PRODUCTS AND APPLICATIONS USING NATIONAL COMPONENTS. PRIOR TO USING OR DISTRIBUTING ANY PRODUCTS THAT INCLUDE NATIONAL COMPONENTS, BUYERS SHOULD PROVIDE ADEQUATE DESIGN, TESTING AND OPERATING SAFEGUARDS.

EXCEPT AS PROVIDED IN NATIONAL'S TERMS AND CONDITIONS OF SALE FOR SUCH PRODUCTS, NATIONAL ASSUMES NO LIABILITY WHATSOEVER, AND NATIONAL DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY RELATING TO THE SALE AND/OR USE OF NATIONAL PRODUCTS INCLUDING LIABILITY OR WARRANTIES RELATING TO FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS PRIOR WRITTEN APPROVAL OF THE CHIEF EXECUTIVE OFFICER AND GENERAL COUNSEL OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

Life support devices or systems are devices which (a) are intended for surgical implant into the body, or (b) support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in a significant injury to the user. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system or to affect its safety or effectiveness.

National Semiconductor and the National Semiconductor logo are registered trademarks of National Semiconductor Corporation. All other brand or product names may be trademarks or registered trademarks of their respective holders.

Copyright© 2010 National Semiconductor Corporation

For the most current product information visit us at www.national.com



National Semiconductor Americas Technical Support Center Email: support@nsc.com Tel: 1-800-272-9959 National Semiconductor Europe Technical Support Center Email: europe.support@nsc.com National Semiconductor Asia Pacific Technical Support Center Email: ap.support@nsc.com

National Semiconductor Japan Technical Support Center Email: jpn.feedback@nsc.com